

## N-Channel 20-V (D-S) 175° MOSFET

### **CHARACTERISTICS**

- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS

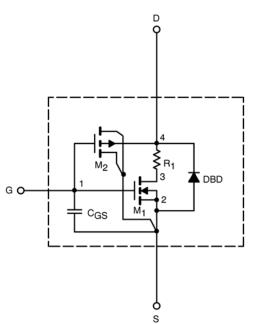
- Apply for both Linear and Switching Application
- Accurate over the -55 to 125°C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

### DESCRIPTION

The attached spice model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the -55 to  $125^{\circ}$ C temperature ranges under the pulsed 0-V to 10-V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

#### SUBCIRCUIT MODEL SCHEMATIC

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.



This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

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# SPICE Device Model SUD50N02-06P **Vishay Siliconix**



SPECIFICATIONS (T <sub>J</sub> = 25°C UN	ILESS OTHERV	VISE NOTED)			
Parameter	Symbol	Test Condition	Simulated Data	Measured Data	Unit
Static					
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}$ = $V_{GS}$ , $I_D$ = 250 $\mu$ A	1.4		V
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS}$ = 5 V, $V_{GS}$ = 10 V	964		А
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	$V_{GS}$ = 10 V, I <sub>D</sub> = 20 A	0.0041	0.0046	Ω
		$V_{GS}$ = 10 V, $I_{D}$ = 20 A, $T_{J}$ = 125°C	0.0057		
		$V_{GS}$ = 4.5 V, I <sub>D</sub> = 20 A	0.0065	0.0073	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	$I_{\rm S}$ = 50 A, $V_{\rm GS}$ = 0 V	0.91	1.2	V
Dynamic <sup>b</sup>					
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1 MHz	2418	2550	pF
Output Capacitance	C <sub>oss</sub>		816	900	
Reverse Transfer Capacitance	C <sub>rss</sub>		348	415	
Total Gate Charge <sup>c</sup>	Qg	$V_{DS}$ = 10 V, $V_{GS}$ = 4.5 V, $I_{D}$ = 50 A	20	19	nC
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>		7.5	7.5	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>		6	6	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	$V_{DD}$ = 10 V, R <sub>L</sub> = 0.20 Ω $I_D \cong 50$ A, $V_{GEN}$ = 10 V, R <sub>G</sub> = 2.5 Ω $I_F$ = 50 A, di/dt = 100 A/μs	11	11	ns
Rise Time <sup>c</sup>	tr		10	10	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>		9	24	
Fall Time <sup>c</sup>	t <sub>f</sub>		9	9	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>		31	35	

Notes

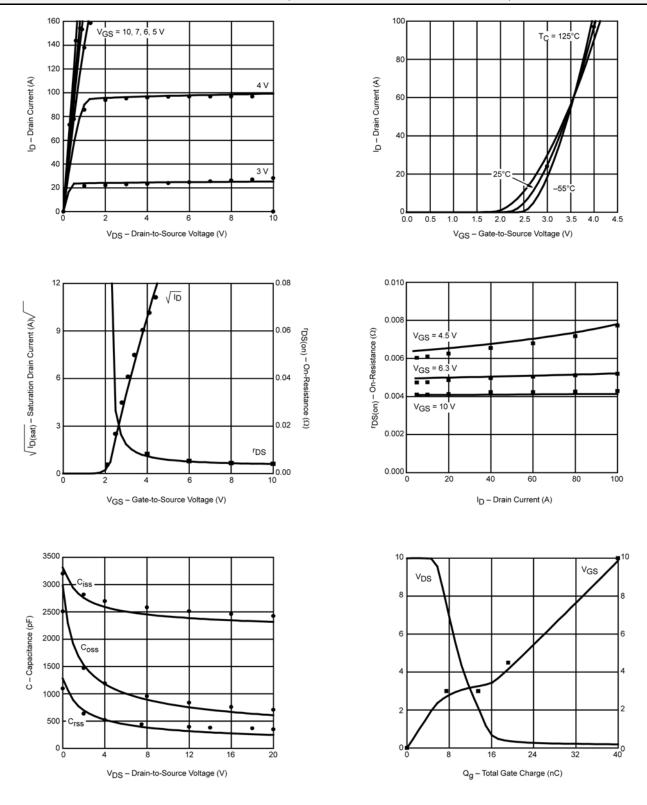
a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2%. b. Guaranteed by design, not subject to production testing. c. Independent of operating temperature.



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COMPARISON OF MODEL WITH MEASURED DATA (TJ=25°C UNLESS OTHERWISE NOTED)



Note: Dots and squares represent measured data.

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